

Silicon NPN Power Transistors

2SC2022

DESCRIPTION

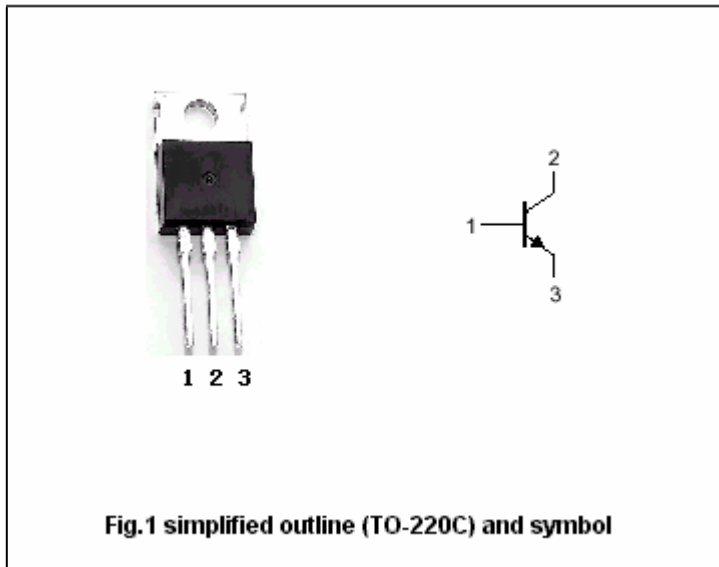
- With TO-220C package
- High voltage

APPLICATIONS

- Series regulator, switch, and general purpose applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	300	V
V _{CEO}	Collector-emitter voltage	Open base	300	V
V _{EBO}	Emitter-base voltage	Open collector	6	V
I _C	Collector current		1	A
P _C	Collector dissipation	T _C =25°C	30	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-50~150	°C

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =25mA ; I _B =0	300			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =1mA ; I _E =0	300			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA ; I _C =0	6			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =500mA ; I _B =100mA			1.0	V
I _{CBO}	Collector cut-off current	V _{CB} =300V ; I _E =0			1.0	mA
I _{EBO}	Emitter cut-off current	V _{EB} =6V ; I _C =0			1.0	mA
h _{FE}	DC current gain	I _C =200m A ; V _{CE} =4V	30			
f _T	Transition frequency	I _C =100mA ; V _{CE} =12V		10		MHz

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PACKAGE OUTLINE

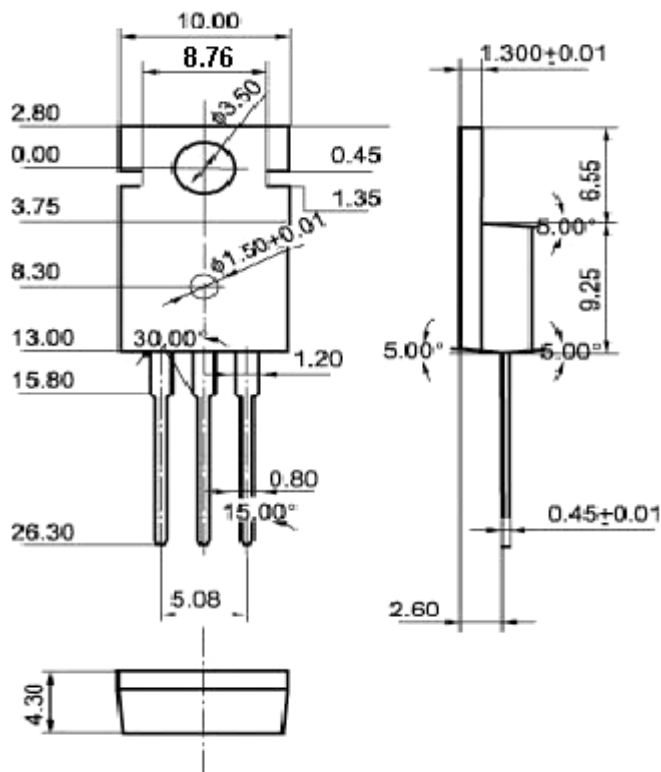


Fig.2 Outline dimensions (unindicated tolerance:±0.10 mm)